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# FOD060L, FOD260L 3.3V/5V High Speed-10 MBit/s Logic Gate Optocouplers

## Features

- FOD060L in SO8 and FOD260L in 8-pin DIP
- Very high speed – 10 MBit/s
- Superior CMR — 50 kV/μs at 1,000V peak
- Fan-out of 8 over -40°C to +85°C
- Logic gate output
- Strobable output
- Wired OR-open collector
- Safety and regulatory approvals
  - UL1577
  - DIN EN/IEC 60747-5-2

## Applications

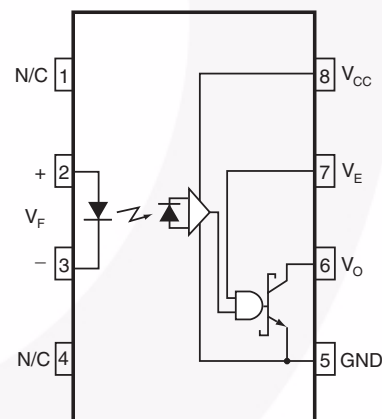
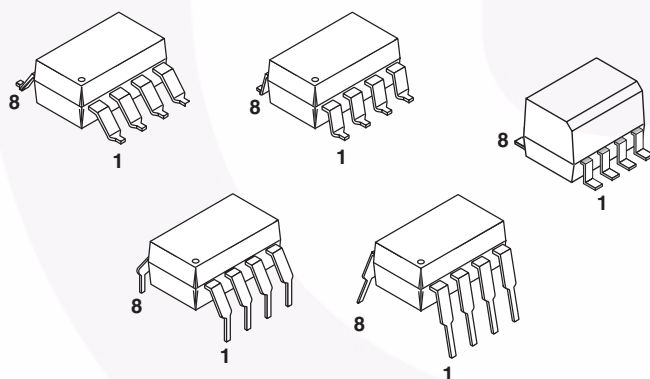
- Ground loop elimination
- LSTTL to TTL, LSTTL or 5-volt CMOS

- Line receiver, data transmission
- Data multiplexing
- Switching power supplies
- Pulse transformer replacement
- Computer-peripheral interface

## Description

These optocouplers consist of an AlGaAs LED, optically coupled to a very high speed integrated photo-detector logic gate. Devices include a strobable output. This output features an open collector, thereby permitting wired OR outputs. The coupled parameters are guaranteed over the temperature range of -40°C to +85°C. A maximum input signal of 5 mA will provide a minimum output sink current of 13 mA (fan out of 8). An internal noise shield provides superior common mode rejection of typically 50 kV/μs at 1,000V common mode.

## Package



## Truth Table (Positive Logic)

| Input | Enable | Output |
|-------|--------|--------|
| On    | H      | L      |
| Off   | H      | H      |
| On    | L      | H      |
| Off   | L      | H      |
| On*   | NC*    | L*     |
| Off*  | NC*    | H*     |

\*Devices with pin 7 not connected.

A 0.1 μF bypass capacitor must be connected between pins 5 and 8. (See Note 1)

**Absolute Maximum Ratings** (No derating required up to 85°C)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

| Symbol                     | Parameter                                                        | Value           | Units |
|----------------------------|------------------------------------------------------------------|-----------------|-------|
| $T_{STG}$                  | Storage Temperature                                              | -40 to +125     | °C    |
| $T_{OPR}$                  | Operating Temperature                                            | -40 to +85      | °C    |
| <b>EMITTER</b>             |                                                                  |                 |       |
| $I_F$                      | DC/Average Forward Input Current                                 | 50              | mA    |
| $V_E$                      | Enable Input Voltage, not to exceed $V_{CC}$ by more than 500 mV | $V_{CC} + 0.5V$ | V     |
| $V_R$                      | Reverse Input Voltage                                            | 5.0             | V     |
| $P_I$                      | Power Dissipation                                                | 45              | mW    |
| <b>DETECTOR</b>            |                                                                  |                 |       |
| $V_{CC}$<br>(1 minute max) | Supply Voltage                                                   | 7.0             | V     |
| $I_O$                      | Output Current                                                   | 50              | mA    |
| $V_O$                      | Output Voltage                                                   | 7.0             | V     |
| $P_O$                      | Collector Output Power Dissipation                               | 85              | mW    |

**Recommended Operating Conditions**

| Symbol   | Parameter                  | Min. | Max.     | Units |
|----------|----------------------------|------|----------|-------|
| $I_{FL}$ | Input Current, Low Level   | 0    | 250      | μA    |
| $I_{FH}$ | Input Current, High Level  | *6.3 | 15       | mA    |
| $V_{CC}$ | Supply Voltage, Output     | 3.0  | 5.5      | V     |
| $V_{EL}$ | Enable Voltage, Low Level  | 0    | 0.8      | V     |
| $V_{EH}$ | Enable Voltage, High Level | 2.0  | $V_{CC}$ | V     |
| $T_A$    | Operating Temperature      | -40  | +85      | °C    |
| N        | Fan Out (TTL load)         |      | 8        |       |
| $R_L$    | Output Pull-up Resistor    | 330  | 4K       | Ω     |

\*6.3 mA is a guard banded value which allows for at least 20% CTR degradation. Initial input current threshold value is 5.0 mA or less.

**Electrical Characteristics** ( $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$  unless otherwise specified. Typical value is measured at  $T_A = 25^\circ\text{C}$  and  $V_{CC} = 3.3\text{V}$ )

**Individual Component Characteristics**

| Symbol                  | Parameter                           | Test Conditions                                                      | Min. | Typ. | Max. | Unit                 |
|-------------------------|-------------------------------------|----------------------------------------------------------------------|------|------|------|----------------------|
| <b>EMITTER</b>          |                                     |                                                                      |      |      |      |                      |
| $V_F$                   | Input Forward Voltage               | $I_F = 10\text{ mA}$<br>$T_A = 25^\circ\text{C}$                     |      | 1.4  | 1.8  | V                    |
| $B_{VR}$                | Input Reverse Breakdown Voltage     | $I_R = 10\text{ }\mu\text{A}$                                        | 5.0  |      | 1.75 | V                    |
| $C_{IN}$                | Input Capacitance                   | $V_F = 0$ , $f = 1\text{ MHz}$                                       |      | 6.0  |      | pF                   |
| $\Delta V_F/\Delta T_A$ | Input Diode Temperature Coefficient | $I_F = 10\text{ mA}$                                                 |      | -1.9 |      | mV/ $^\circ\text{C}$ |
| <b>DETECTOR</b>         |                                     |                                                                      |      |      |      |                      |
| $I_{CCH}$               | High Level Supply Current           | $V_E = 0.5\text{ V}$ , $I_F = 0\text{ mA}$ , $V_{CC} = 3.3\text{ V}$ |      | 3.5  | 7    | mA                   |
| $I_{CCL}$               | Low Level Supply Current            | $V_E = 0.5\text{ V}$ , $I_F = 0\text{ mA}$ , $V_{CC} = 3.3\text{ V}$ |      | 3.2  | 10   | mA                   |
| $I_{EL}$                | Low Level Enable Current            | $V_{CC} = 3.3\text{ V}$ , $V_E = 0.5\text{ V}$                       |      |      | -1.6 | mA                   |
| $I_{EH}$                | High Level Enable Current           | $V_{CC} = 3.3\text{ V}$ , $V_E = 2.0\text{ V}$                       |      |      | -1.6 | mA                   |
| $V_{EH}$                | High Level Enable Voltage           | $V_{CC} = 3.3\text{ V}$ , $I_F = 10\text{ mA}$                       | 2.0  | 1.27 |      | V                    |
| $V_{EL}$                | Low Level Enable Voltage            | $V_{CC} = 3.3\text{ V}$ , $I_F = 10\text{ mA}$ (Note 2)              |      | 1.18 | 0.8  | V                    |

**Switching Characteristics** ( $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$ ,  $V_{CC} = 3.3\text{ V}$ ,  $I_F = 7.5\text{ mA}$  unless otherwise specified. Typical value is measured at  $T_A = 25^\circ\text{C}$  and  $V_{CC} = 3.3\text{V}$ )

| Symbol                | AC Characteristics                                    | Test Conditions                                                                                                                                               | Min.   | Typ.   | Max. | Unit             |
|-----------------------|-------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------|--------|--------|------|------------------|
| $T_{PLH}$             | Propagation Delay Time to Output High Level           | $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Fig. 9) (Note 3)                                                                                                    |        | 65     | 90   | ns               |
| $T_{PHL}$             | Propagation Delay Time to Output Low Level            | $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Fig. 9) (Note 4)                                                                                                    |        | 43     | 75   | ns               |
| $ T_{PHL} - T_{PLH} $ | Pulse Width Distortion                                | $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Fig. 9)                                                                                                             |        | 23     | 25   | ns               |
| $t_{PSK}$             | Propagation Delay Skew                                | $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Note 5)                                                                                                             |        | 31     | 40   | ns               |
| $t_r$                 | Output Rise Time (10-90%)                             | $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Fig. 9)(Note 6)                                                                                                     |        | 22     |      | ns               |
| $t_f$                 | Output Fall Time (90-10%)                             | $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Fig. 12) (Note 7)                                                                                                   |        | 3      |      | ns               |
| $t_{ELH}$             | Enable Propagation Delay Time to Output High Level    | $V_{EH} = 3\text{ V}$ , $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Fig. 10) (Note 8)                                                                           |        | 47     |      | ns               |
| $t_{EHL}$             | Enable Propagation Delay Time to Output Low Level     | $V_{EH} = 3\text{ V}$ , $R_L = 350\Omega$ , $C_L = 15\text{ pF}$ (Fig. 10) (Note 9)                                                                           |        | 27     |      | ns               |
| $CM_H$                | Common Mode Transient Immunity (at Output High Level) | $R_L = 350\Omega$ , $T_A = 25^\circ\text{C}$ , $I_F = 0\text{ mA}$ , $V_{OH}(\text{Min.}) = 2.0\text{ V}$ , $ V_{CM}  = 1,000\text{ V}$ (Fig. 11) (Note 10)   | 25,000 | 50,000 |      | V/ $\mu\text{s}$ |
| $CM_L$                | Common Mode Transient Immunity (at Output Low Level)  | $R_L = 350\Omega$ , $T_A = 25^\circ\text{C}$ , $I_F = 7.5\text{ mA}$ , $V_{OL}(\text{Max.}) = 0.8\text{ V}$ , $ V_{CM}  = 1,000\text{ V}$ (Fig. 11) (Note 11) | 25,000 | 50,000 |      | V/ $\mu\text{s}$ |

**Transfer Characteristics** ( $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$  Unless otherwise specified. Typical value is measured at  $T_A = 25^\circ\text{C}$  and  $V_{CC} = 3.3\text{V}$ )

| Symbol   | DC Characteristics        | Test Conditions                                                                                              | Min. | Typ. | Max. | Unit          |
|----------|---------------------------|--------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| $I_{OH}$ | High Level Output Current | $I_F = 250\ \mu\text{A}$ , $V_{CC} = 3.3\ \text{V}$ , $V_O = 3.3\ \text{V}$ , $V_E = 2.0\ \text{V}$ (Note 2) |      | 0.01 | 50   | $\mu\text{A}$ |
| $V_{OL}$ | Low Level Output Voltage  | $V_{CC} = 3.3\ \text{V}$ , $I_F = 5\ \text{mA}$ , $I_{OL} = 13\ \text{mA}$ , $V_E = 2.0\ \text{V}$ (Note 2)  |      | 0.3  | 0.6  | V             |
| $I_{FT}$ | Input Threshold Current   | $V_{CC} = 3.3\ \text{V}$ , $V_O = 0.6\ \text{V}$ , $I_{OL} = 13\ \text{mA}$ , $V_E = 2.0\ \text{V}$ (Note 2) |      | 1    | 5    | mA            |

**Isolation Characteristics** ( $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$  Unless otherwise specified. Typical value is measured at  $T_A = 25^\circ\text{C}$  and  $V_{CC} = 3.3\text{V}$ )

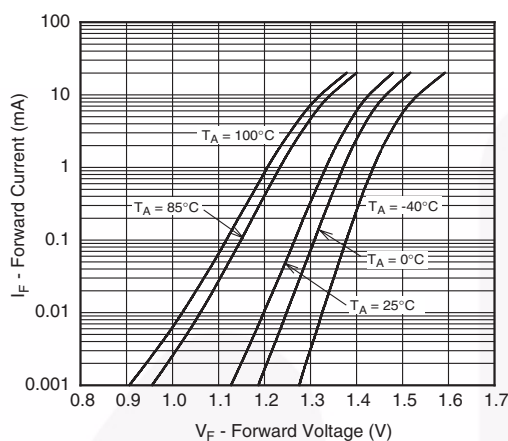
| Symbol    | Characteristics                                             | Test Conditions                                                                                                      | Min. | Typ.      | Max. | Unit          |
|-----------|-------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------|------|-----------|------|---------------|
| $I_{I-O}$ | Input-Output Insulation Leakage Current                     | Relative humidity = 45%,<br>$T_A = 25^\circ\text{C}$ , $t = 5\ \text{s}$ ,<br>$V_{I-O} = 3000\ \text{VDC}$ (Note 12) |      |           | 1.0  | $\mu\text{A}$ |
| $V_{ISO}$ | Withstand Insulation Test Voltage<br><br>FOD060L<br>FOD260L | $I_{IO} \leq 2\ \mu\text{A}$ , $R_H < 50\%$ ,<br>$T_A = 25^\circ\text{C}$ , $t = 1\ \text{min.}$ (Note 12)           | 3750 |           |      | $V_{RMS}$     |
|           |                                                             |                                                                                                                      | 5000 |           |      |               |
| $R_{I-O}$ | Resistance (Input to Output)                                | $V_{I-O} = 500\ \text{V}$ (Note 12)                                                                                  |      | $10^{12}$ |      | $\Omega$      |
| $C_{I-O}$ | Capacitance (Input to Output)                               | $f = 1\ \text{MHz}$ (Note 12)                                                                                        |      | 0.6       |      | pF            |

#### Notes

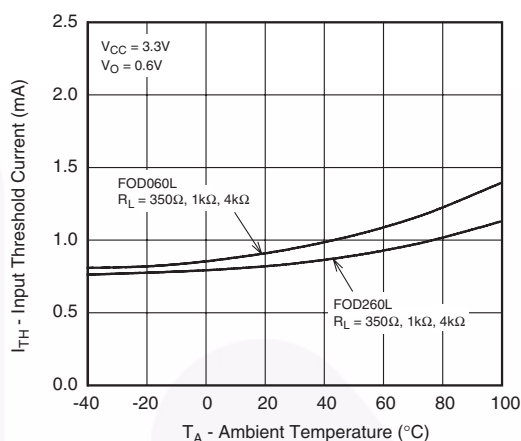
1. The  $V_{CC}$  supply to each optoisolator must be bypassed by a  $0.1\ \mu\text{F}$  capacitor or larger. This can be either a ceramic or solid tantalum capacitor with good high frequency characteristic and should be connected as close as possible to the package  $V_{CC}$  and GND pins of each device.
2. Enable Input – No pull up resistor required as the device has an internal pull up resistor.
3.  $t_{PLH}$  – Propagation delay is measured from the 3.75 mA level on the HIGH to LOW transition of the input current pulse to the 1.5V level on the LOW to HIGH transition of the output voltage pulse.
4.  $t_{PHL}$  – Propagation delay is measured from the 3.75 mA level on the LOW to HIGH transition of the input current pulse to the 1.5V level on the HIGH to LOW transition of the output voltage pulse.
5.  $t_{PSK}$  is the worst case difference between  $t_{PHL}$  and  $t_{PLH}$  for any devices at the stated test conditions.
6.  $t_r$  – Rise time is measured from the 90% to the 10% levels on the LOW to HIGH transition of the output pulse.
7.  $t_f$  – Fall time is measured from the 10% to the 90% levels on the HIGH to LOW transition of the output pulse.
8.  $t_{ELH}$  – Enable input propagation delay is measured from the 1.5V level on the HIGH to LOW transition of the input voltage pulse to the 1.5V level on the LOW to HIGH transition of the output voltage pulse.
9.  $t_{EHL}$  – Enable input propagation delay is measured from the 1.5V level on the LOW to HIGH transition of the input voltage pulse to the 1.5V level on the HIGH to LOW transition of the output voltage pulse.
10.  $CM_H$  – The maximum tolerable rate of rise of the common mode voltage to ensure the output will remain in the high state (i.e.,  $V_{OUT} > 2.0\ \text{V}$ ). Measured in volts per microsecond (V/ $\mu\text{s}$ ).
11.  $CM_L$  – The maximum tolerable rate of fall of the common mode voltage to ensure the output will remain in the low output state (i.e.,  $V_{OUT} < 0.8\ \text{V}$ ). Measured in volts per microsecond (V/ $\mu\text{s}$ ).
12. Device considered a two-terminal device: Pins 1, 2, 3 and 4 shorted together, and Pins 5, 6, 7 and 8 shorted together.

## Typical Performance Curves

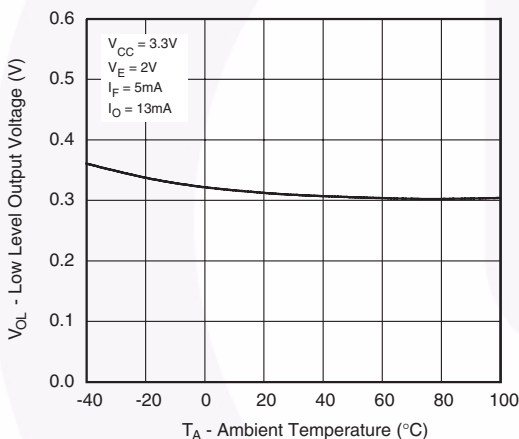
**Fig. 1 Input Forward Current vs. Forward Voltage**



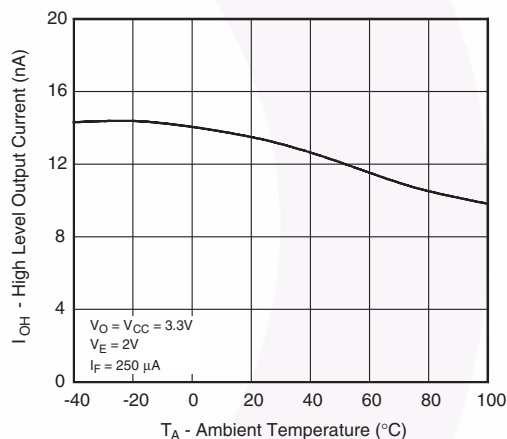
**Fig. 2 Input Threshold Current vs. Ambient Temperature**



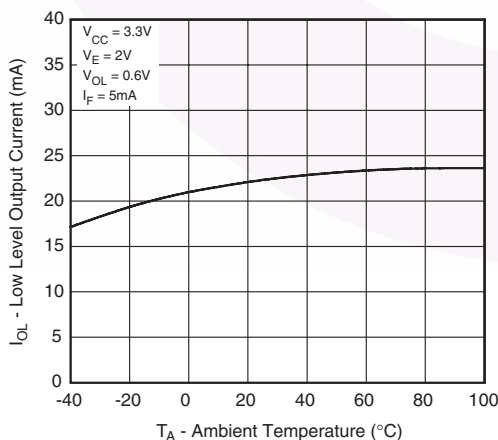
**Fig. 3 Low Level Output Voltage vs. Ambient Temperature**



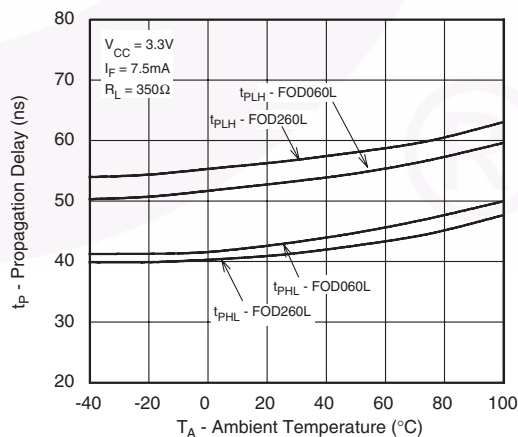
**Fig. 4 High Level Output Current vs. Ambient Temperature**



**Fig. 5 Low Level Output Current vs. Ambient Temperature**

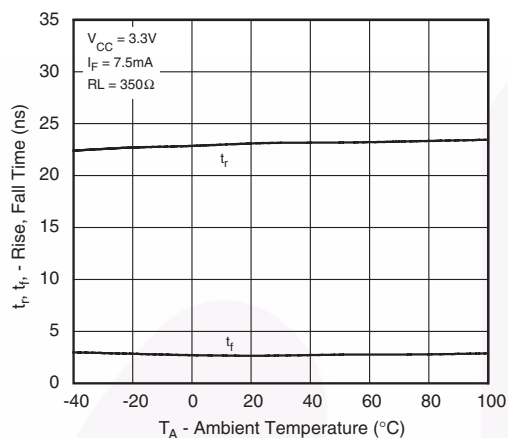


**Fig. 6 Propagation Delay vs. Ambient Temperature**

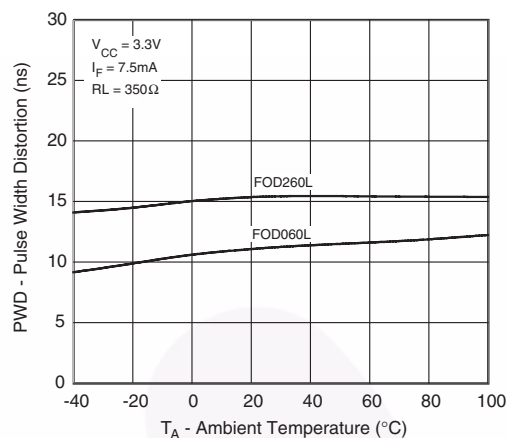


## Typical Performance Curves

**Fig. 7 Rise and Fall Times vs. Ambient Temperature**



**Fig. 8 Pulse Width Distortion vs. Ambient Temperature**



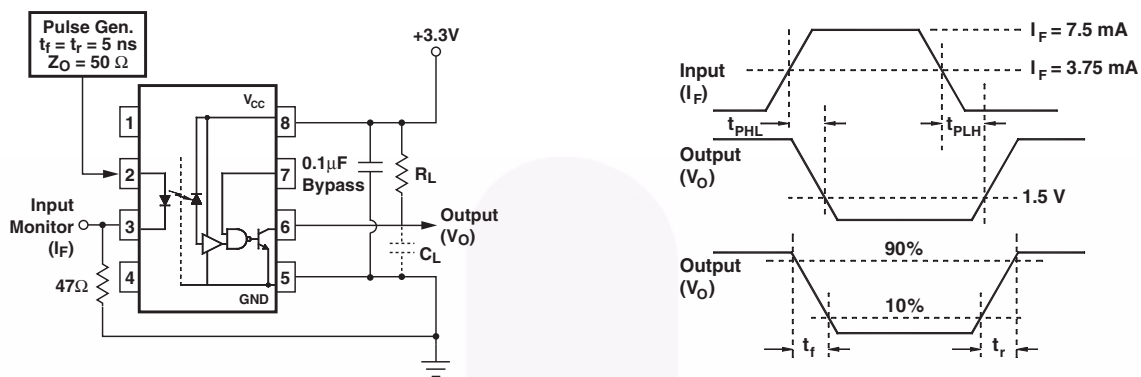


Fig. 9 Test Circuit and Waveforms for  $t_{PLH}$ ,  $t_{PHL}$ ,  $t_r$  and  $t_f$ .

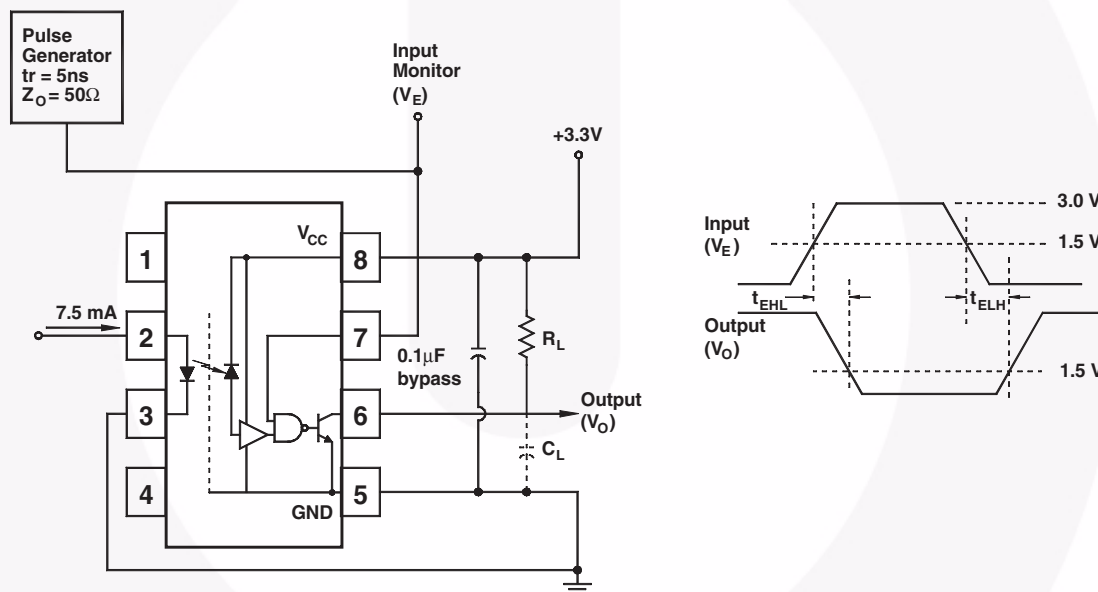


Fig. 10 Test Circuit  $t_{EHL}$  and  $t_{ELH}$ .

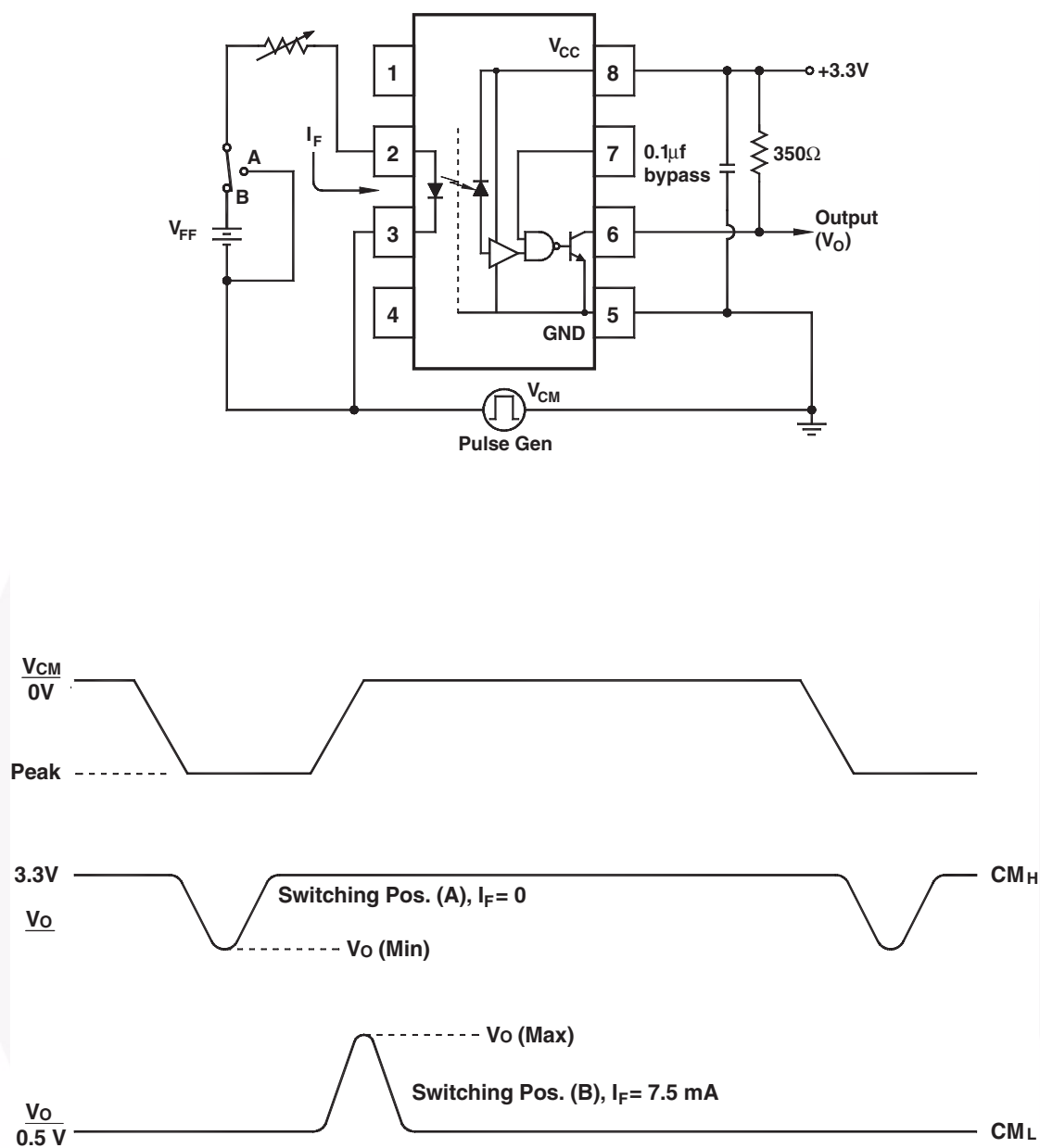


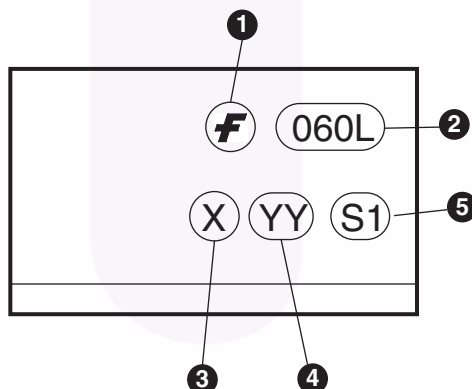
Fig. 11 Test Circuit Common Mode Transient Immunity

## Ordering Information

| Part Number  | Package                                                   | Packing Method                       |
|--------------|-----------------------------------------------------------|--------------------------------------|
| FOD060L      | Small outline 8-pin                                       | Tube (50 units per tube)             |
| FOD060LR2    | Small outline 8-pin                                       | Tape and Reel (2,500 units per reel) |
| FOD260L      | DIP 8-Pin                                                 | Tube (50 units per tube)             |
| FOD260LS     | SMT 8-Pin (Lead Bend)                                     | Tube (50 units per tube)             |
| FOD260LSD    | SMT 8-Pin (Lead Bend)                                     | Tape and Reel (1,000 units per reel) |
| FOD260LV     | DIP 8-Pin, DIN EN/IEC 60747-5-2 option                    | Tube (50 units per tube)             |
| FOD260LSV    | SMT 8-Pin (Lead Bend), DIN EN/IEC 60747-5-2 option        | Tube (50 units per tube)             |
| FOD260LSDV   | SMT 8-Pin (Lead Bend), DIN EN/IEC 60747-5-2 option        | Tape and Reel (1,000 units per reel) |
| FOD260LTV    | DIP 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-2 option | Tube (50 units per tube)             |
| FOD260LTSV   | SMT 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-2 option | Tube (50 units per tube)             |
| FOD260LTSR2  | SMT 8-Pin, 0.4" Lead Spacing                              | Tape and Reel (700 units per reel)   |
| FOD260LTSR2V | SMT 8-Pin, 0.4" Lead Spacing, DIN EN/IEC 60747-5-2 option | Tape and Reel (700 units per reel)   |

## Marking Information

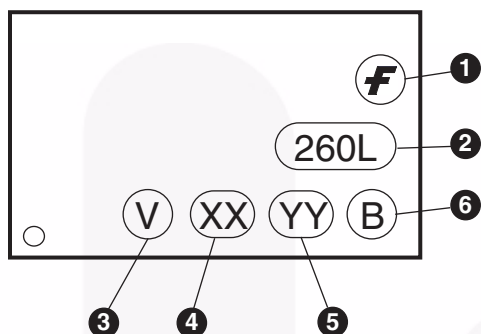
### Small Outline



| Definitions |                                               |
|-------------|-----------------------------------------------|
| 1           | Fairchild logo                                |
| 2           | Device number                                 |
| 3           | One digit year code, e.g., '8'                |
| 4           | Two digit work week ranging from '01' to '53' |
| 5           | Assembly package code                         |

## Marking Information (Continued)

### DIP and SMT

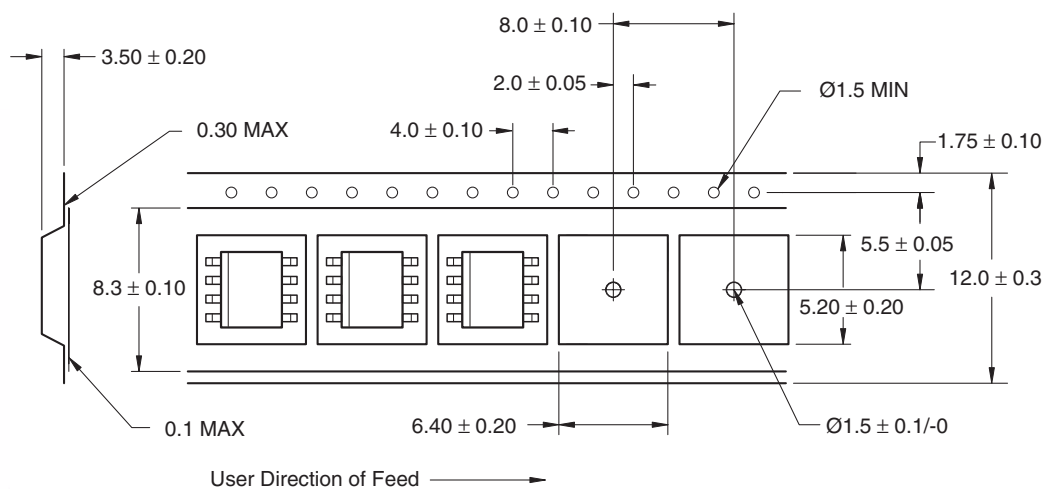


#### Definitions

|   |                                                                                                         |
|---|---------------------------------------------------------------------------------------------------------|
| 1 | Fairchild logo                                                                                          |
| 2 | Device number                                                                                           |
| 3 | VDE mark (Note: Only appears on parts ordered with DIN EN/IEC 60747-5-2 option – See order entry table) |
| 4 | Two digit year code, e.g., '11'                                                                         |
| 5 | Two digit work week ranging from '01' to '53'                                                           |
| 6 | Assembly package code                                                                                   |

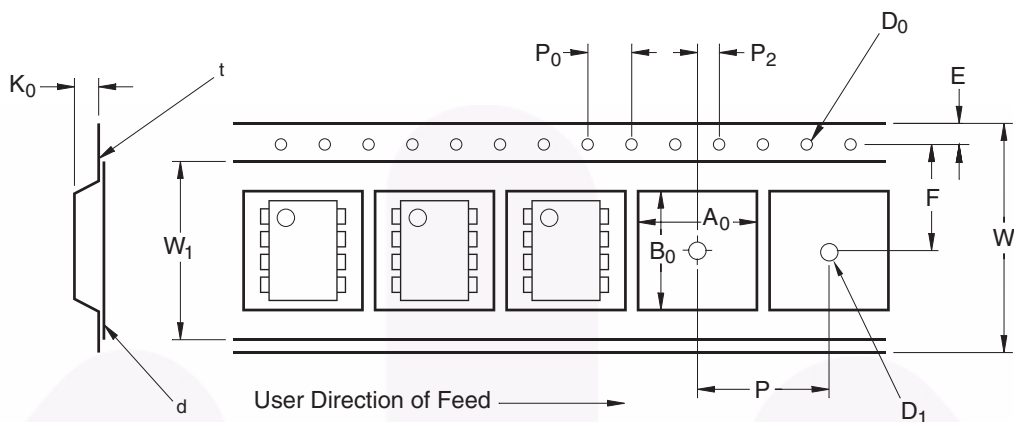
## Carrier Tape Specification

### Small Outline

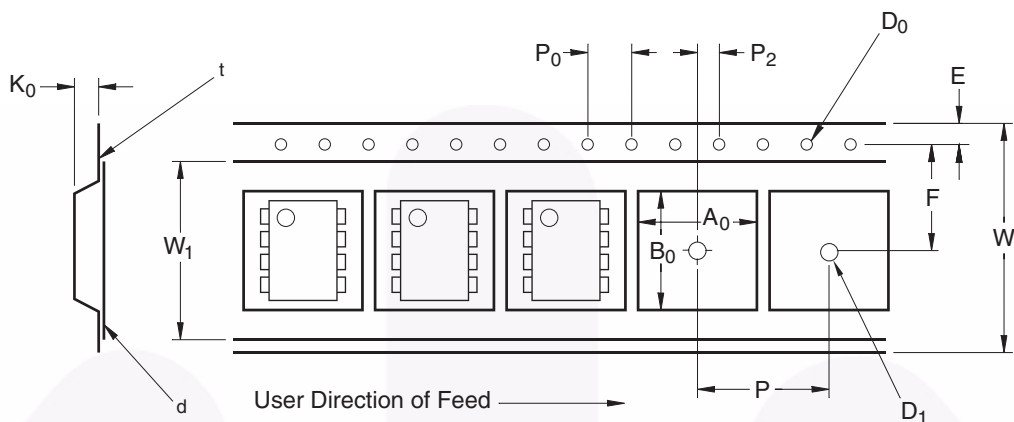


**Note:**

All dimensions are in millimeters.

**Carrier Tape Specification** (Continued)**Option S**

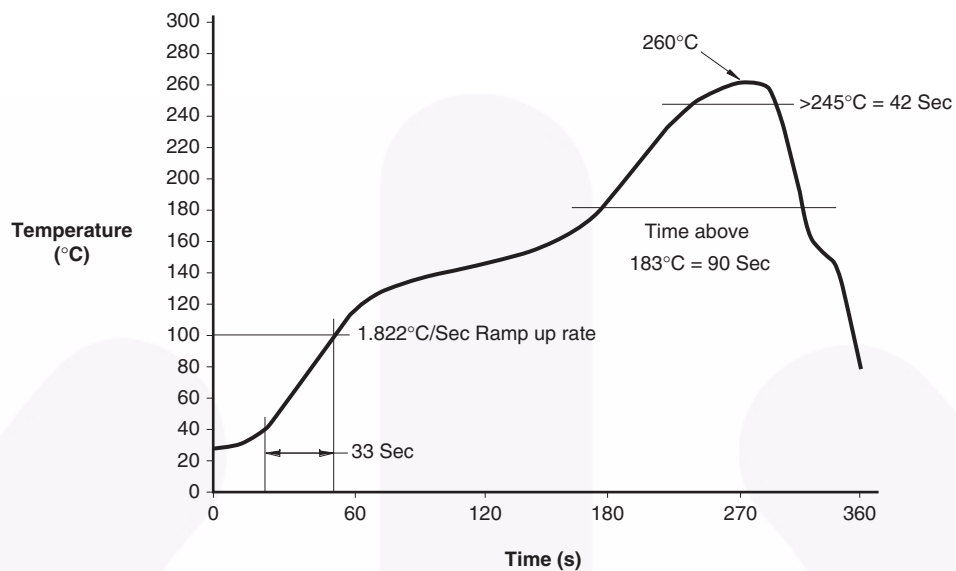
| Symbol         | Description                     | Dimension in mm |
|----------------|---------------------------------|-----------------|
| W              | Tape Width                      | 16.0 ± 0.3      |
| t              | Tape Thickness                  | 0.30 ± 0.05     |
| P <sub>0</sub> | Sprocket Hole Pitch             | 4.0 ± 0.1       |
| D <sub>0</sub> | Sprocket Hole Diameter          | 1.55 ± 0.05     |
| E              | Sprocket Hole Location          | 1.75 ± 0.10     |
| F              | Pocket Location                 | 7.5 ± 0.1       |
| P <sub>2</sub> |                                 | 2.0 ± 0.1       |
| P              | Pocket Pitch                    | 12.0 ± 0.1      |
| A <sub>0</sub> | Pocket Dimensions               | 10.30 ± 0.20    |
| B <sub>0</sub> |                                 | 10.30 ± 0.20    |
| K <sub>0</sub> |                                 | 4.90 ± 0.20     |
| W <sub>1</sub> | Cover Tape Width                | 13.2 ± 0.2      |
| d              | Cover Tape Thickness            | 0.1 max         |
|                | Max. Component Rotation or Tilt | 10°             |
| R              | Min. Bending Radius             | 30              |

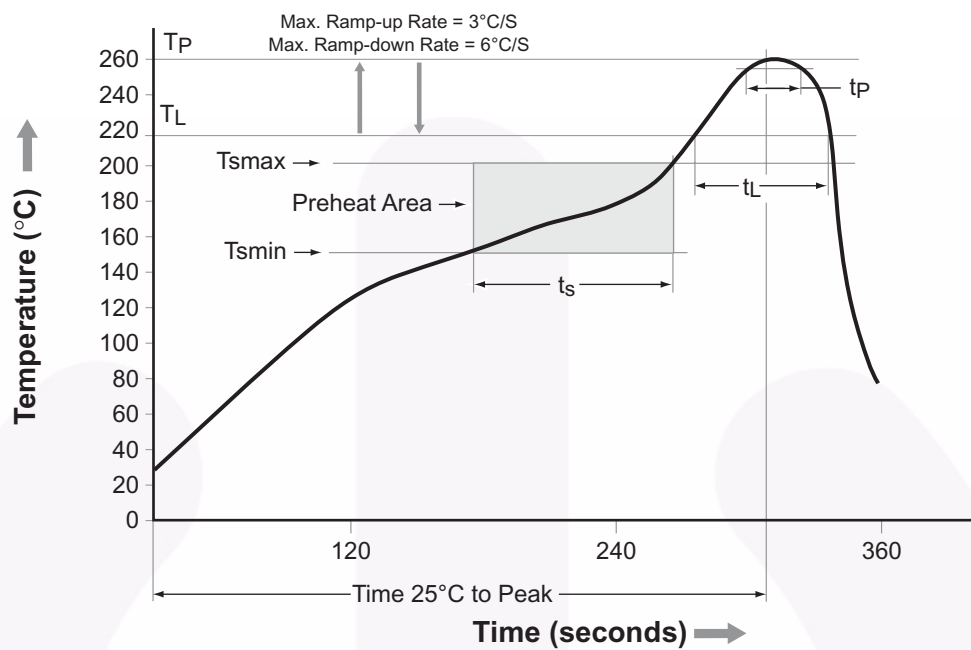
**Carrier Tape Specification** (Continued)**Option TS**

| Symbol         | Description                     | Dimension in mm |
|----------------|---------------------------------|-----------------|
| W              | Tape Width                      | 24.0 ± 0.3      |
| t              | Tape Thickness                  | 0.40 ± 0.1      |
| P <sub>0</sub> | Sprocket Hole Pitch             | 4.0 ± 0.1       |
| D <sub>0</sub> | Sprocket Hole Diameter          | 1.55 ± 0.05     |
| E              | Sprocket Hole Location          | 1.75 ± 0.10     |
| F              | Pocket Location                 | 11.5 ± 0.1      |
| P <sub>2</sub> |                                 | 2.0 ± 0.1       |
| P              | Pocket Pitch                    | 16.0 ± 0.1      |
| A <sub>0</sub> | Pocket Dimensions               | 12.80 ± 0.1     |
| B <sub>0</sub> |                                 | 10.35 ± 0.1     |
| K <sub>0</sub> |                                 | 5.7 ± 0.1       |
| W <sub>1</sub> | Cover Tape Width                | 21.0 ± 0.1      |
| d              | Cover Tape Thickness            | 0.1 max         |
|                | Max. Component Rotation or Tilt | 10°             |
| R              | Min. Bending Radius             | 30              |

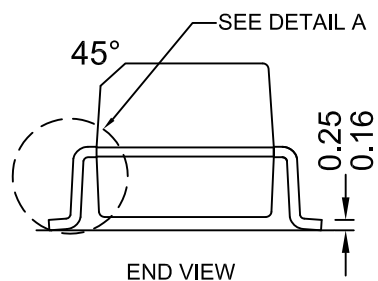
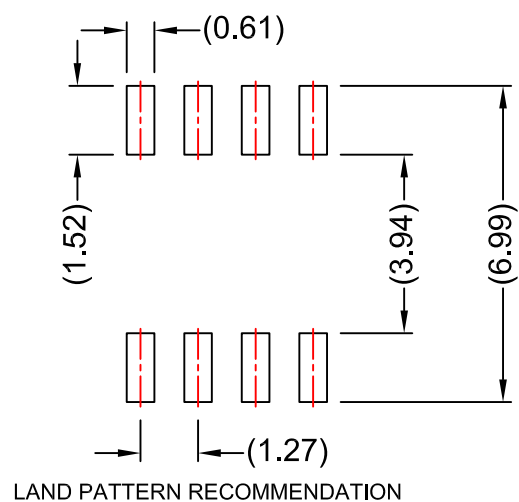
## Reflow Profile

### Small Outline



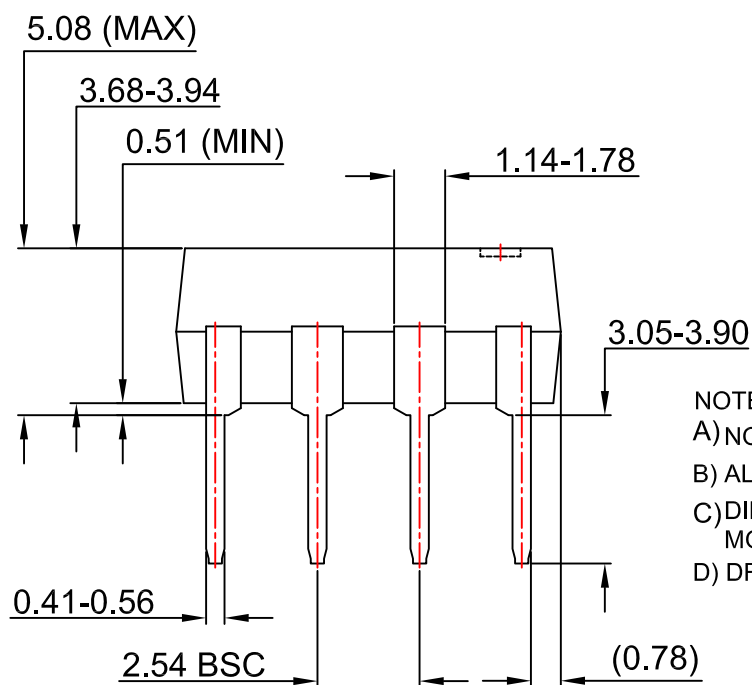
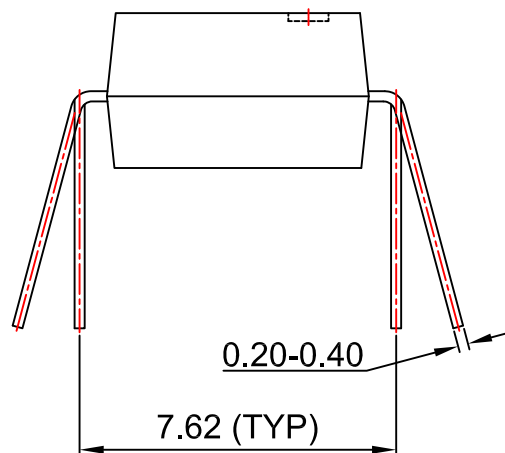
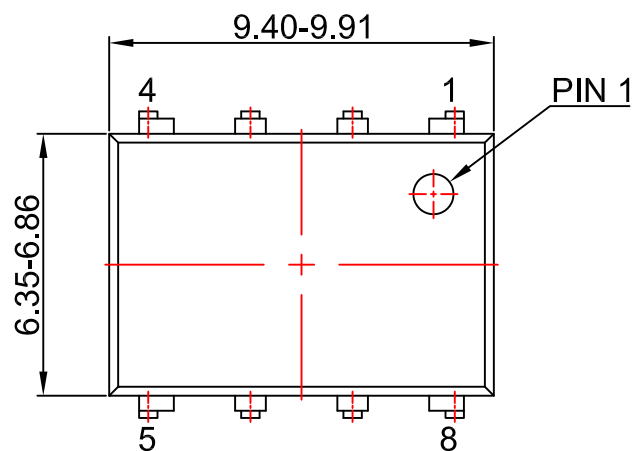
**Reflow Profile** (Continued)**DIP and SMT**

| Profile Feature                                  | Pb-Free Assembly Profile |
|--------------------------------------------------|--------------------------|
| Temperature Min. ( $T_{smin}$ )                  | 150°C                    |
| Temperature Max. ( $T_{smax}$ )                  | 200°C                    |
| Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ ) | 60–120 seconds           |
| Ramp-up Rate ( $t_L$ to $t_p$ )                  | 3°C/second max.          |
| Liquidous Temperature ( $T_L$ )                  | 217°C                    |
| Time ( $t_L$ ) Maintained Above ( $T_L$ )        | 60–150 seconds           |
| Peak Body Package Temperature                    | 260°C +0°C / -5°C        |
| Time ( $t_p$ ) within 5°C of 260°C               | 30 seconds               |
| Ramp-down Rate ( $T_P$ to $T_L$ )                | 6°C/second max.          |
| Time 25°C to Peak Temperature                    | 8 minutes max.           |



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B) ALL DIMENSIONS ARE IN MILLIMETERS.  
C) DIMENSIONS DO NOT INCLUDE MOLD  
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D) LANDPATTERN STANDARD: SOIC127P600X175-8M.  
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NOTES:

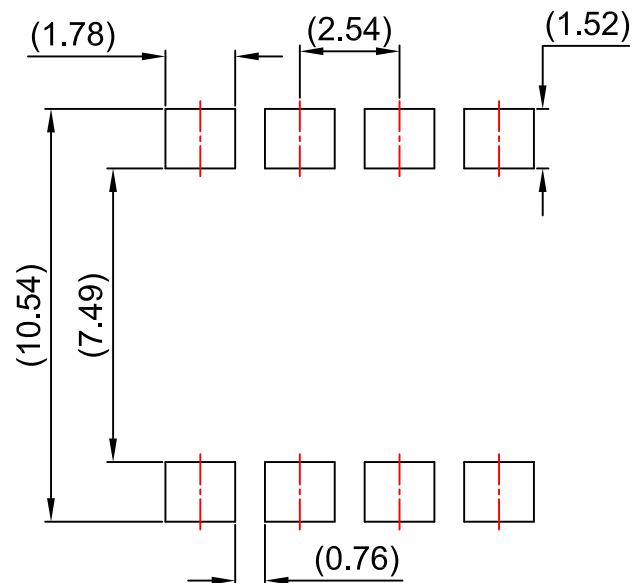
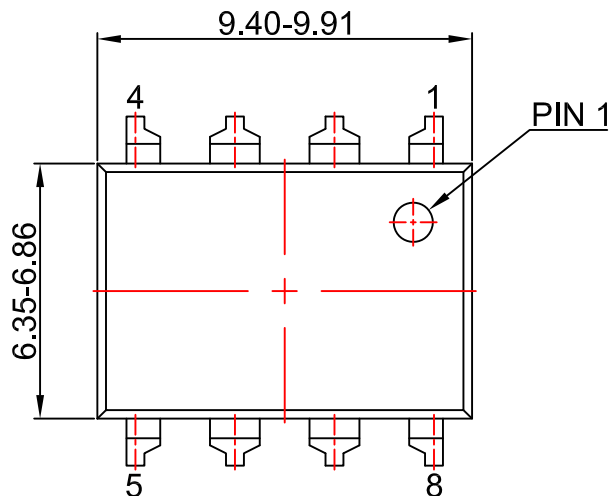
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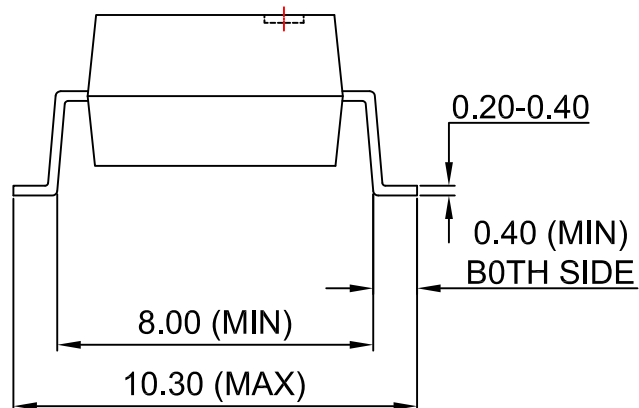
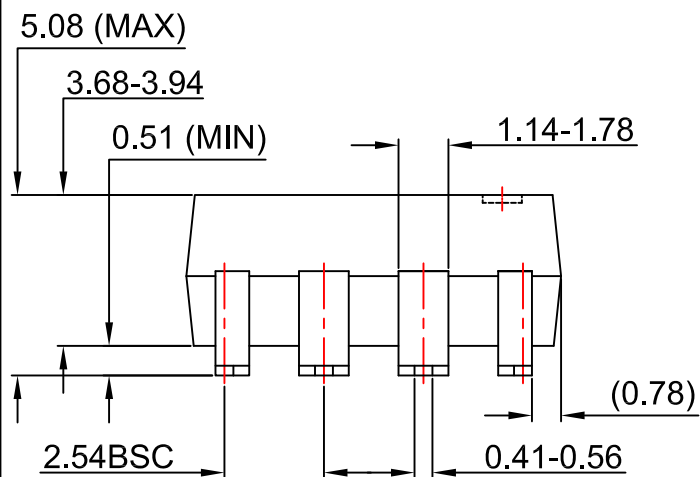
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